



Major Ratings and Characteristics

$I_{F(AV)}$	1.0 A
V_{RRM}	80 V to 200 V
I_{FSM}	30 A
V_F	0.85V
$T_j \text{ max.}$	150 °C

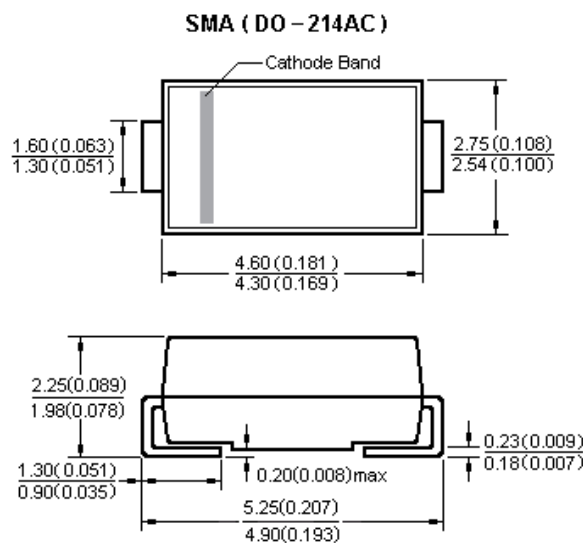


Features

- Low profile package
- Ideal for automated placement
- Ultrafast reverse recovery time
- Low power losses, high efficiency
- Low forward voltage drop
- High surge capability
- High temperature soldering:
260°C/10 seconds at terminals
- Component in accordance to
RoHS 2002/95/1 and WEEE 2002/96/EC

Mechanical Date

- Case: JEDEC DO-214AC molded plastic body over passivated chip
- Terminals: Solder plated, solderable per J-STD-002B and JESD22-B102D
- Polarity: Laser band denotes cathode end



Dimensions in millimeters and (inches)

Maximum Ratings & Thermal Characteristics & Electrical Characteristics

($T_A = 25\text{ °C}$ unless otherwise noted)

	Symbol	SS18	SS110	SS1150	SS1200	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	80	100	150	200	V
Maximum RMS voltage	V_{RMS}	56	70	105	140	V
Maximum DC blocking voltage	V_{DC}	80	100	150	200	V
Maximum average forward rectified current	$I_{F(AV)}$	1				A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	30				A
Maximum instantaneous forward voltage at 1.0A	V_F	0.85				V
Maximum DC reverse current at Rated DC blocking voltage	I_R	$T_A = 25\text{ °C}$ 0.5				mA
		$T_A = 100\text{ °C}$ 5				mA
Voltage rate of change (rated VR)	dv/dt	10000				V/ μ s
Thermal resistance from junction to ambient	$R_{\theta JA}$	88				°C/W
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to +150				°C